



## **Load Switch with Level-Shift**

PRODUCT SUMMARY				
V <sub>DS2</sub> (V)	$V_{DS2}(V)$ $R_{DS(on)}(\Omega)$			
1.8 to 8	0.060 at V <sub>IN</sub> = 4.5 V	2.9		
	0.100 at V <sub>IN</sub> = 2.5 V	2.2		
	0.175 at V <sub>IN</sub> = 1.8 V	1.7		

#### **DESCRIPTION**

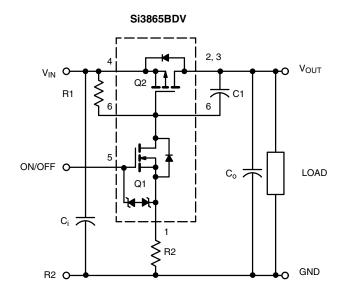
The Si3865BDV includes a p- and n-channel MOSFET in a single TSOP-6 package. The low on-resistance p-channel TrenchFET® is tailored for use as a load switch. The n-channel, with an external resistor, can be used as a levelshift to drive the p-channel load-switch. The n-channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5 V. The Si3865BDV operates on supply lines from 1.8 V to 8 V, and can drive loads up to 2.9 A.

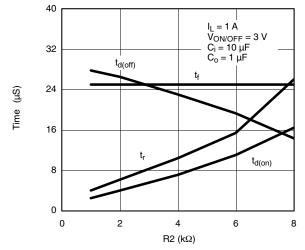
#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 **Definition**
- 60 mΩ Low  $R_{DS(on)}$  TrenchFET<sup>®</sup>: 1.8 V Rated
- 1.8 V to 8 V Input
- 1.5 V to 8 V Logic Level Control
- Low Profile, Small Footprint TSOP-6 Package
- 3000 V ESD Protection On Input Switch, VON/OFF
- Adjustable Slew-Rate
- Compliant to RoHS Directive 2002/95/EC

# COMPLIANT **HALOGEN** FREE

#### **APPLICATION CIRCUITS**





Note: For R2 switching variations with other V<sub>IN</sub>/R1 combinations See Typical Characteristics

**Switching Variation** R2 at  $V_{IN} = 2.5 \text{ V}$ , R1 = 20 k $\Omega$ 

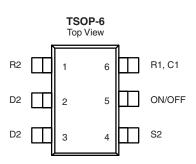
COMPONENTS					
R1	Pull-Up Resistor	Typical 10 k $\Omega$ to 1 M $\Omega^*$			
R2	Optional Slew-Rate Control	Typical 0 to 100 kΩ*			
C1	Optional Slew-Rate Control	Typical 1000 pF			

<sup>\*</sup> Minimum R1 value should be at least 10 x R2 to ensure Q1 turn-on.

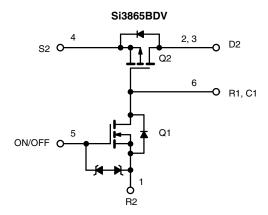
The Si3865BDV is ideally suited for high-side load switching in portable applications. The integrated N-Channel level-shift device saves space by reducing external components. The slew rate is set externally so that rise-times can be tailored to different load types.

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#### **FUNCTIONAL BLOCK DIAGRAM**



Ordering Information: Si3865BDV-T1-E3 (Lead (Pb)-free) Si3865BDV-T1-GE3 (Lead (Pb)-free and Halogen-free)



<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>A</sub> = 25 °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Input Voltage On/Off Voltage		$V_{IN}$	8	V
		V <sub>ON/OFF</sub>	8	\ \ \
Load Current	Continuous <sup>a, b</sup>	Ι <sub>L</sub>	± 2.9	
Load Current	Pulsed <sup>b, c</sup>		± 6	А
Continuous Intrinsic Diode Conduction <sup>a</sup>		I <sub>S</sub>	- 1	
Maximum Power Dissipation <sup>a</sup>		$P_{D}$	0.83	W
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C
ESD Rating, MIL-STD-883D Human Body Model (100 pF, 1500 Ω)		ESD	3	kV

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient (continuous current) <sup>a</sup>	R <sub>thJA</sub>	125	150	°C/W	
Maximum Junction-to-Foot (Q2)	R <sub>thJC</sub>	40	55	]	

<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)								
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Off Characteristics								
Reverse Leakage Current	I <sub>FL</sub>	$V_{IN} = 8 \text{ V}, V_{ON/OFF} =$			1	μΑ		
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> = - 1 A			- 0.77	- 1	V	
OnN Characteristics								
Input Voltage Range	V <sub>IN</sub>		1.8		8	V		
	R <sub>DS(on)</sub>	V <sub>ON/OFF</sub> = 1.5 V, I <sub>D</sub> = 1 A	V <sub>IN</sub> = 4.5 V		0.045	0.060	Ω	
On-Resistance (P-Channel) at 1 A			V <sub>IN</sub> = 2.5 V		0.075	0.100		
			V <sub>IN</sub> = 1.8 V		0.135	0.175		
On-State (P-Channel) Drain-Current	,	$V_{IN-OUT} \le 0.2 \text{ V}, V_{IN} = 5 \text{ V}, V_{ON/OFF} = 1.5 \text{ V}$		1			Α	
	I <sub>D(on)</sub>	$V_{IN-OUT} \le 0.3 \text{ V}, V_{IN} = 3 \text{ V}, V_{ON/OFF} = 1.5 \text{ V}$		1			] ^	

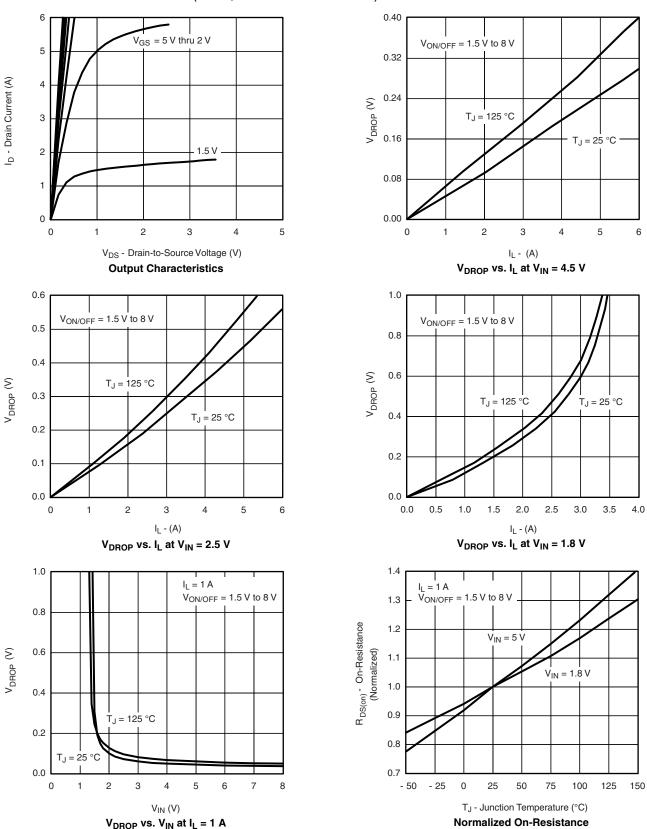
- a. Surface Mounted on FR4 board.
- b.  $V_{IN}$  = 8 V,  $V_{ON/OFF}$  = 8 V,  $T_A$  = 25 °C. c. Pulse test: pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

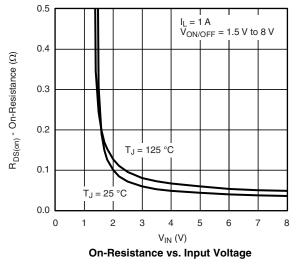


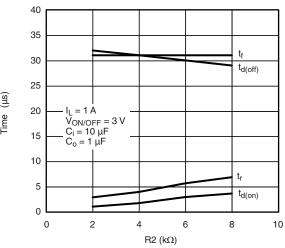
vs. Junction Temperature

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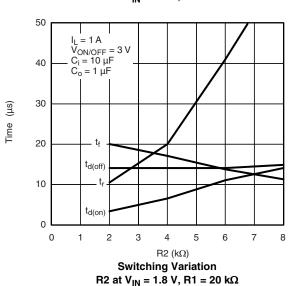
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# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

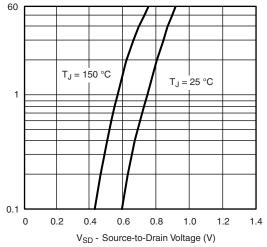




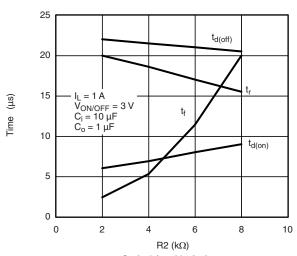
Switching Variation R2 at  $V_{IN}$  = 4.5 V, R1 = 20 k $\Omega$ 



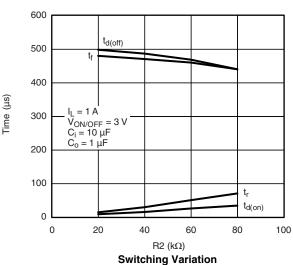
Is - Source Current (A)



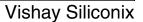
Source-Drain Diode Forward Voltage



Switching Variation R2 at  $V_{IN}$  = 2.5 V, R1 = 20 k $\Omega$ 

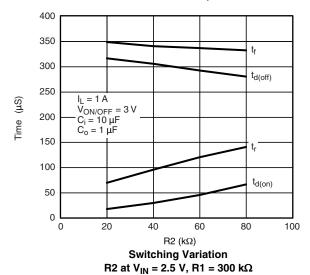


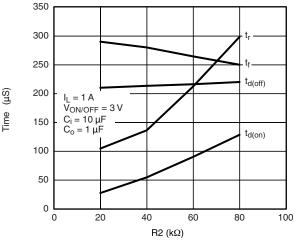
R2 at  $V_{IN} = 4.5 \text{ V}$ , R1 = 300 k $\Omega$ 



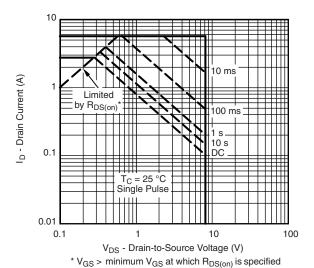


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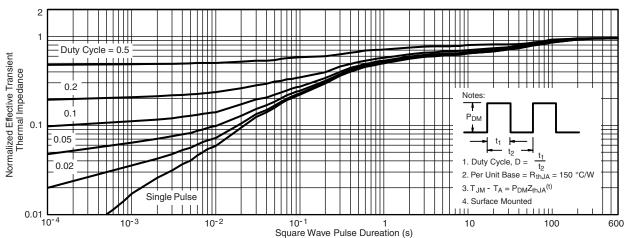




Switching Variation R2 at V  $_{\text{IN}}$  = 1.8 V, R1 = 300 k $\Omega$ 



#### Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient

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